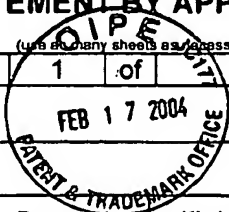


Substitute for form 1449A/PTO & 1449B/PTO		Complete if Known	
FIRST INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/622,484
		Filing Date	July 21, 2003
		First Named Inventor	Michael SETTON
		Examiner Name	Unassigned <i>Pompey</i>
		Attorney Docket Number	015290-755
Sheet	1 of 2		



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Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
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RP	60-107838		JAPAN	06-13-1985		

NON-PATENT LITERATURE DOCUMENTS	
Examiner Initials	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>RP</i>	Alers, G.B. et al., "Nitrogen plasma annealing for low temperature Ta ₂ O ₅ films", Applied Physics Letters, vol. 72, no. 11, 1308-1310, 16 March 1998
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Examiner Signature	<i>Ron Pompey</i>	Date Considered	<i>12/17/04</i>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Substitute for form 1449A/PTO & 1449B/PTO		Complete if Known	
FIRST INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use in main sheet as necessary)		Application Number	10/622,484
		Filing Date	July 21, 2003
		First Named Inventor	Michael SETTON
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Sheet	2 of 2	Attorney Docket Number	015290-755

FEB 17 2004 PATENT & TRADEMARK OFFICE		NON-PATENT LITERATURE DOCUMENTS
Examiner Initials	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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Examiner Signature	Date Considered
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